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Kind regards,

Team Nexperia



40 V, 200 mA NPN/NPN general-purpose double transistor
Rev. 01 — 12 May 2009 Product data s

Product data sheet

## 1. Product profile

### 1.1 General description

NPN/NPN general-purpose double transistor in a SOT363 (SC-88) very small Surface-Mounted Device (SMD) plastic package.

Table 1. **Product overview** 

Type number	Package				Package
	NXP	JEITA	complement	complement	configuration
PMBT3904YS	SOT363	SC-88	PMBT3906YS	PMBT3946YPN	very small

#### 1.2 Features

- General-purpose double transistor
- Board-space reduction

### 1.3 Applications

■ General-purpose switching and amplification

#### 1.4 Quick reference data

Table 2. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Per transistor						
$V_{CEO}$	collector-emitter voltage	open base	-	-	40	V
I <sub>C</sub>	collector current		-	-	200	mA
h <sub>FE</sub>	DC current gain	$V_{CE} = 1 V;$ $I_{C} = 10 \text{ mA}$	100	180	300	



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### 40 V, 200 mA NPN/NPN general-purpose double transistor

#### **Pinning information** 2.

Table 3. **Pinning** 

	3		
Pin	Description	Simplified outline	Graphic symbol
1	emitter TR1		2 5 4
2	base TR1	6 5 4	6 5 4
3	collector TR2		TR2
4	emitter TR2	0	(TR1)
5	base TR2	□1 □2 □3	
6	collector TR1		1 2 3
			sym020

#### **Ordering information** 3.

Table 4. **Ordering information** 

Type number	Package		
	Name	Description	Version
PMBT3904YS	SC-88	plastic surface-mounted package; 6 leads	SOT363

#### **Marking** 4.

**Product data sheet** 

Table 5. **Marking codes** 

Type number	Marking code <sup>[1]</sup>
PMBT3904YS	BC*

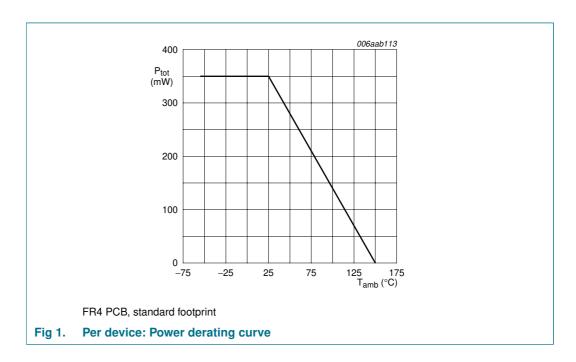
- [1] \* = -: made in Hong Kong
  - \* = p: made in Hong Kong
  - \* = t: made in Malaysia
  - \* = W: made in China

## 5. Limiting values

**Table 6.** Limiting values
In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
Per transist	or				
V <sub>CBO</sub>	collector-base voltage	open emitter	-	60	V
$V_{CEO}$	collector-emitter voltage	open base	-	40	V
$V_{EBO}$	emitter-base voltage	open collector	-	6	V
Ic	collector current		-	200	mA
I <sub>CM</sub>	peak collector current	single pulse; $t_p \le 1 \text{ ms}$	-	200	mA
I <sub>BM</sub>	peak base current	single pulse; $t_p \le 1 \text{ ms}$	-	100	mA
P <sub>tot</sub>	total power dissipation	$T_{amb} \le 25  ^{\circ}C$	[1] -	230	mW
Per device					
P <sub>tot</sub>	total power dissipation	$T_{amb} \le 25  ^{\circ}C$	[1] -	350	mW
Tj	junction temperature		-	150	°C
T <sub>amb</sub>	ambient temperature		-55	+150	°C
T <sub>stg</sub>	storage temperature		-65	+150	°C

<sup>[1]</sup> Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.



## 6. Thermal characteristics

Table 7. Thermal characteristics

Per transistor  R <sub>th(j-a)</sub> thermal resistance from in free air in	Table 1. The	illiai Characteristics					
$\begin{array}{cccccccccccccccccccccccccccccccccccc$	Symbol	Parameter	Conditions	Min	Тур	Max	Unit
junction to ambient $R_{th(j\text{-sp})} \qquad \begin{array}{c} \text{junction to ambient} \\ \text{R}_{th(j\text{-sp})} \\ \text{punction to solder point} \end{array} \qquad \begin{array}{c} \text{-} \\ \text{-} \\ \text{290} \\ \text{K/W} \\ \end{array}$	Per transistor						
junction to solder point	$R_{th(j-a)}$		in free air	[1] -	-	543	K/W
$R_{th(j-a)}$ thermal resistance from in free air [1] 357 K/W	$R_{th(j-sp)}$			-	-	290	K/W
- initig-a)	Per device						
	$R_{th(j-a)}$		in free air	[1] -	-	357	K/W

<sup>[1]</sup> Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

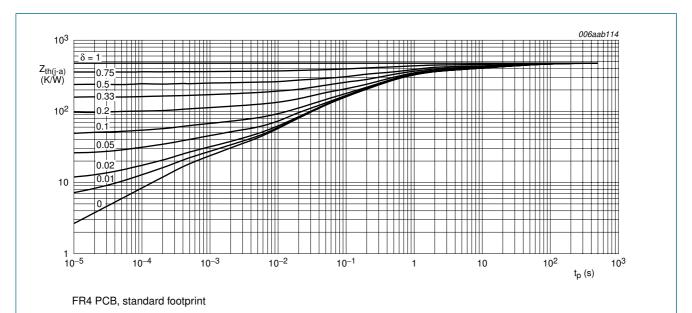


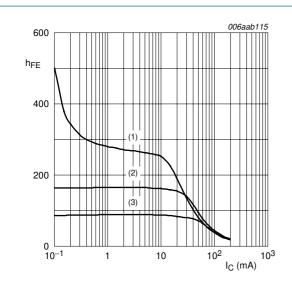
Fig 2. Per transistor: Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

## 7. Characteristics

Table 8. Characteristics

 $T_{amb} = 25 \,^{\circ}C$  unless otherwise specified.

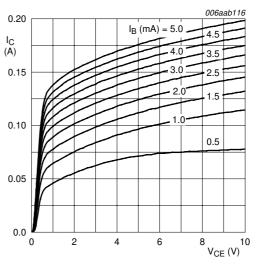
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Per trans	sistor					
I <sub>CBO</sub>	collector-base cut-off current	$V_{CB} = 30 \text{ V}; I_E = 0 \text{ A}$	-	-	50	nA
I <sub>EBO</sub>	emitter-base cut-off current	$V_{EB} = 6 \text{ V}; I_{C} = 0 \text{ A}$	-	-	50	nA
h <sub>FE</sub>	DC current gain	V <sub>CE</sub> = 1 V				
		$I_C = 0.1 \text{ mA}$	60	180	-	
		I <sub>C</sub> = 1 mA	80	180	-	
		I <sub>C</sub> = 10 mA	100	180	300	
		I <sub>C</sub> = 50 mA	60	105	-	
		I <sub>C</sub> = 100 mA	30	50	-	
V <sub>CEsat</sub>	collector-emitter	$I_C = 10 \text{ mA}; I_B = 1 \text{ mA}$	-	75	200	mV
	saturation voltage	$I_C = 50 \text{ mA}; I_B = 5 \text{ mA}$	-	120	300	mV
V <sub>BEsat</sub> base-emitter saturation voltage	$I_C = 10 \text{ mA}; I_B = 1 \text{ mA}$	650	750	850	mV	
	saturation voltage	$I_C = 50 \text{ mA}; I_B = 5 \text{ mA}$	-	850	950	mV
f <sub>T</sub>	transition frequency	$V_{CE} = 20 \text{ V}; I_{C} = 10 \text{ mA};$ f = 100 MHz	300	-	-	MHz
Cc	collector capacitance	$V_{CB} = 5 \text{ V}; I_E = i_e = 0 \text{ A};$ f = 1 MHz	-	-	4	pF
C <sub>e</sub>	emitter capacitance	$V_{BE} = 0.5 \text{ V}; I_C = I_c = 0 \text{ A};$ f = 1 MHz	-	-	8	pF
NF	noise figure	$V_{CE} = 5 \text{ V}; I_{C} = 100 \mu\text{A};$ $R_{S} = 1 \text{ k}\Omega;$ f = 10  Hz to  15.7  kHz	-	-	5	dB
t <sub>d</sub>	delay time	$V_{CC} = 3 \text{ V}; I_{C} = 10 \text{ mA};$	-	-	35	ns
t <sub>r</sub>	rise time	$I_{Bon} = 1 \text{ mA}; I_{Boff} = -1 \text{ mA}$	-	-	35	ns
t <sub>on</sub>	turn-on time	_	-	-	70	ns
ts	storage time		-	-	200	ns
t <sub>f</sub>	fall time		-	-	50	ns
t <sub>off</sub>	turn-off time		-	-	250	ns



$$V_{CE} = 1 V$$

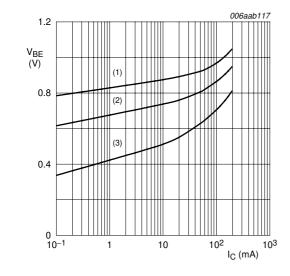
- (1)  $T_{amb} = 150 \, ^{\circ}C$
- (2)  $T_{amb} = 25 \, ^{\circ}C$
- (3)  $T_{amb} = -55 \, ^{\circ}C$

Fig 3. DC current gain as a function of collector current; typical values



 $T_{amb} = 25 \, ^{\circ}C$ 

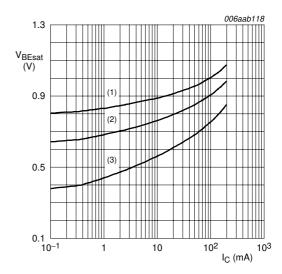
Fig 4. Collector current as a function of collector-emitter voltage; typical values





- (1)  $T_{amb} = -55 \,^{\circ}C$
- (2)  $T_{amb} = 25 \, ^{\circ}C$
- (3)  $T_{amb} = 150 \, ^{\circ}C$

Fig 5. Base-emitter voltage as a function of collector current; typical values

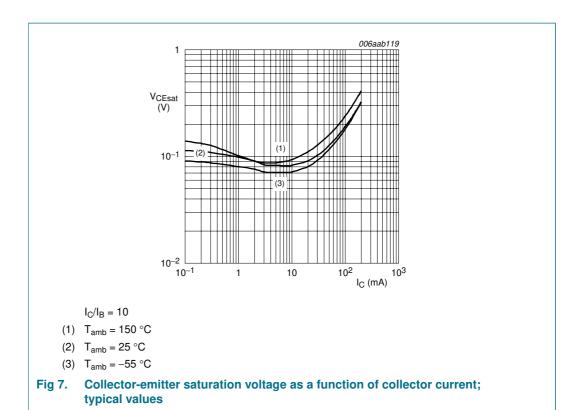


 $I_{C}/I_{B} = 10$ 

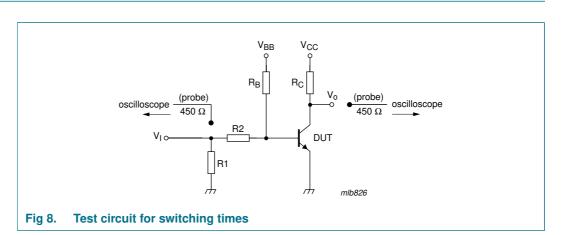
- (1)  $T_{amb} = -55 \, ^{\circ}C$
- (2)  $T_{amb} = 25 \, ^{\circ}C$
- (3)  $T_{amb} = 150 \, ^{\circ}C$

Fig 6. Base-emitter saturation voltage as a function of collector current; typical values

### 40 V, 200 mA NPN/NPN general-purpose double transistor

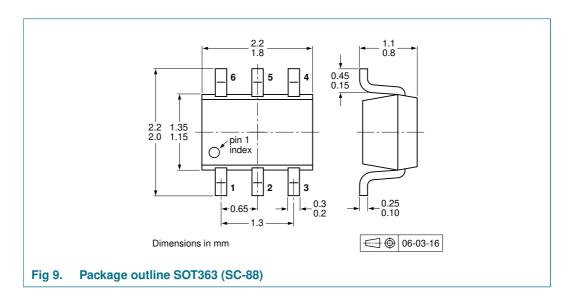


## 8. Test information





## 9. Package outline



## 10. Packing information

Table 9. Packing methods

The indicated -xxx are the last three digits of the 12NC ordering code.[1]

Type number	Package	Description		Packing quantity	
				3000	10000
PMBT3904YS	SOT363	4 mm pitch, 8 mm tape and reel; T1	[2]	-115	-135
		4 mm pitch, 8 mm tape and reel; T2	[3]	-125	-165

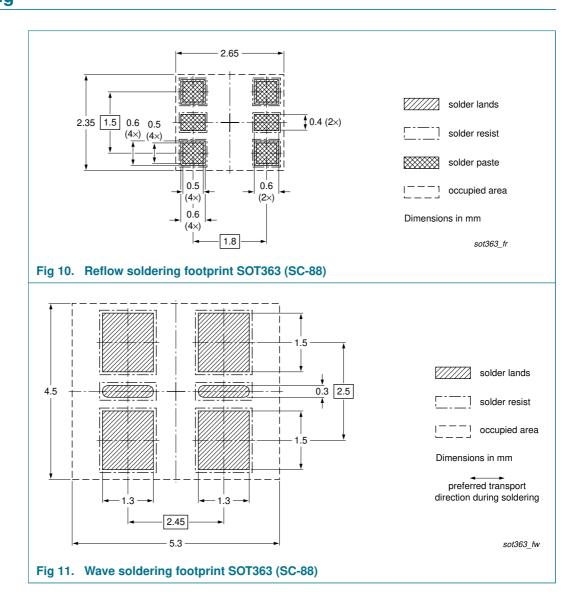
[1] For further information and the availability of packing methods, see Section 14.

[2] T1: normal taping

[3] T2: reverse taping

40 V, 200 mA NPN/NPN general-purpose double transistor

## 11. Soldering





## 12. Revision history

### Table 10. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
PMBT3904YS_1	20090512	Product data sheet	-	-

### 13. Legal information

#### 13.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions"
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### 40 V, 200 mA NPN/NPN general-purpose double transistor

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